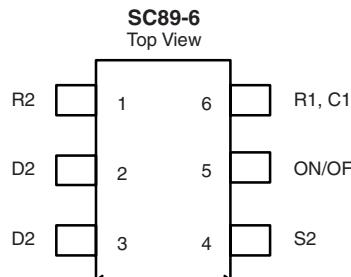
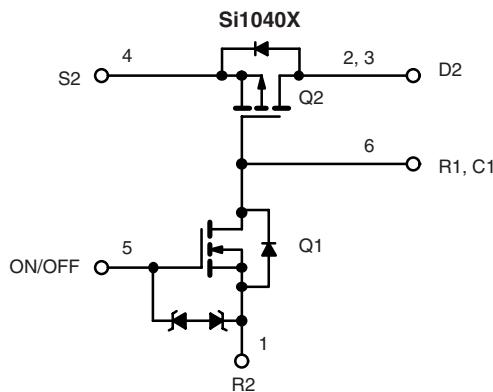


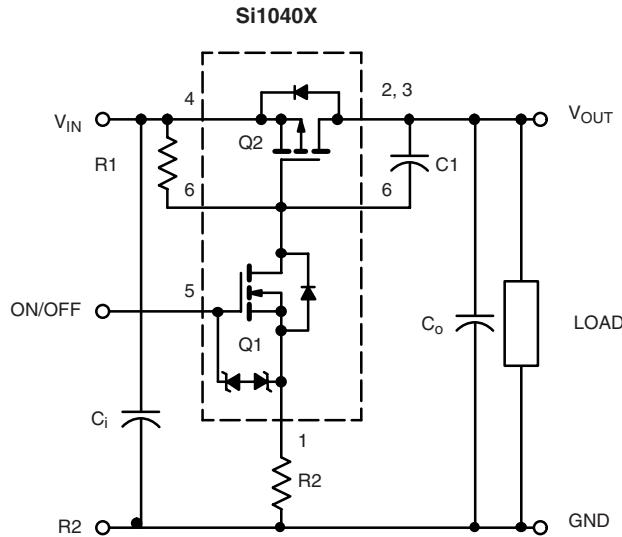
Load Switch with Level-Shift

PRODUCT SUMMARY		
V_{DS2} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
1.8 to 8	0.625 at $V_{IN} = 4.5$ V	± 0.43
	0.890 at $V_{IN} = 2.5$ V	± 0.36
	1.25 at $V_{IN} = 1.8$ V	± 0.3



Ordering Information: Si1040X-T1-E3 (Lead (Pb)-free)
Si1040X-T1-GE3 (Lead (Pb)-free and Halogen-free)

TYPICAL APPLICATION CIRCUIT



FEATURES

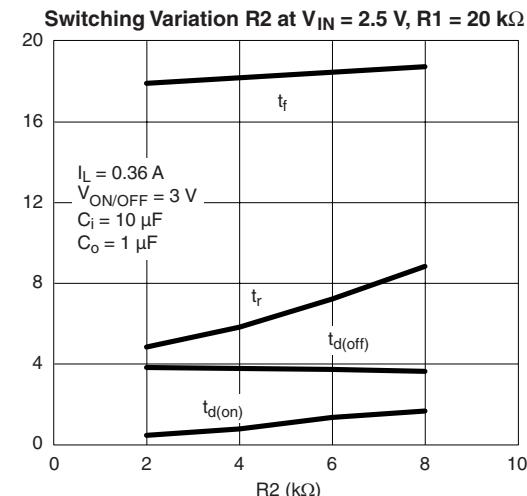
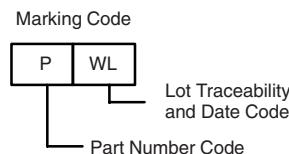
- Halogen-free Option Available
- TrenchFET® Power MOSFET
- 1.8 to 8 V Input
- 1.5 to 8 V Logic Level Control
- Smallest LITTLE FOOT® Package: 1.6 mm x 1.6 mm
- 2000 V ESD Protection On Input Switch, $V_{ON/OFF}$
- Adjustable Slew-Rate



RoHS
COMPLIANT

DESCRIPTION

The Si1040X includes a P- and N-Channel MOSFET in a single SC89-6 package. The low on-resistance P-Channel TrenchFET is tailored for use as a load switch. The N-Channel, with an external resistor, can be used as a level-shift to drive the P-Channel load-switch. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1040X operates on supply lines from 1.8 V to 8 V, and can drive loads up to 0.43 A.



Note: For R2 switching variations with other V_{IN} /R1 combinations See Typical Characteristics

COMPONENTS

R1	Pull-Up Resistor	Typical 10 kΩ to 1 mΩ ^a
R2	Optional Slew-Rate Control	Typical 0 to 100 kΩ ^a
C1	Optional Slew-Rate Control	Typical 1000 pF

Notes:

a. Minimum R1 value should be at least 10 x R2 to ensure Q1 turns on.

The Si1040X is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Input Voltage	V_{IN}	8	V
ON/OFF Voltage	$V_{ON/OFF}$	8	
Load Current	I_L	± 0.43	A
		± 1.0	
Continuous Intrinsic Diode Conduction ^a	I_S	- 0.15	
Maximum Power Dissipation ^a	P_D	0.174	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	2	kV

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (Continuous Current) ^a	R_{thJA}	600	720	°C/W
Maximum Junction-to-Foot (Q2)	R_{thJC}	450	540	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

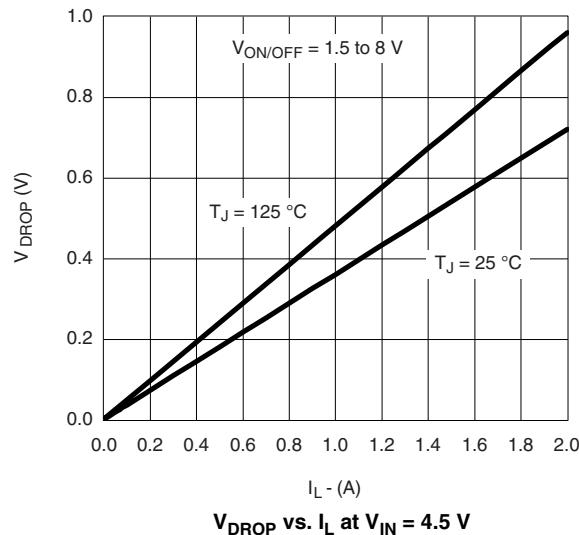
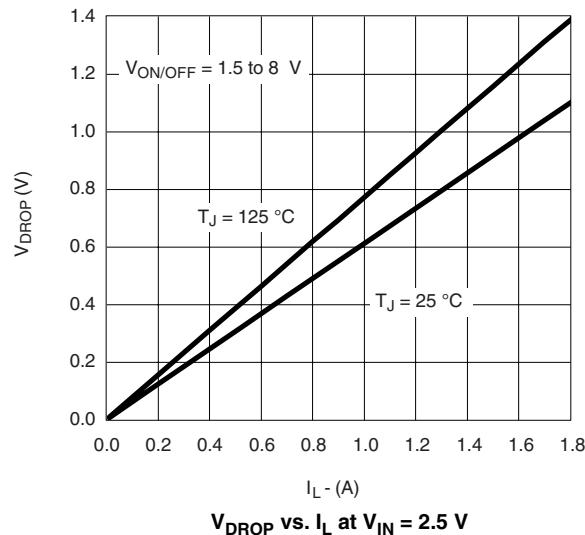
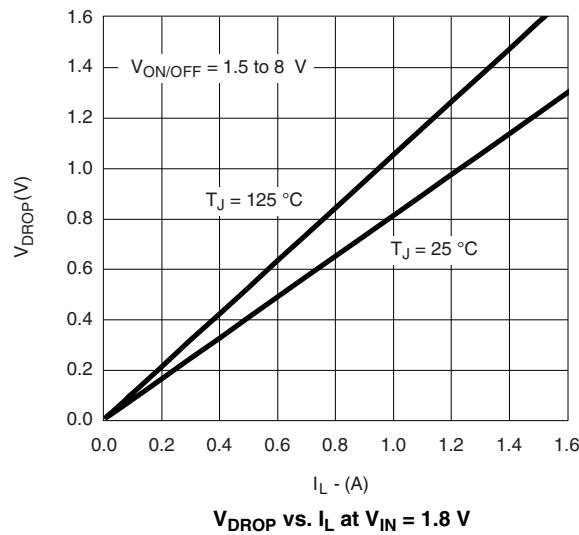
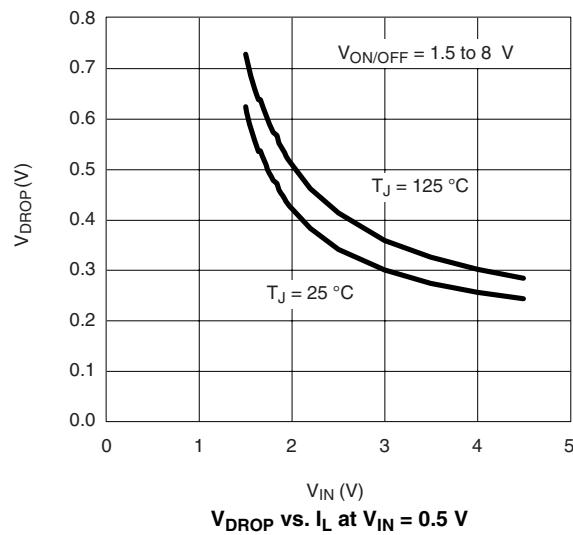
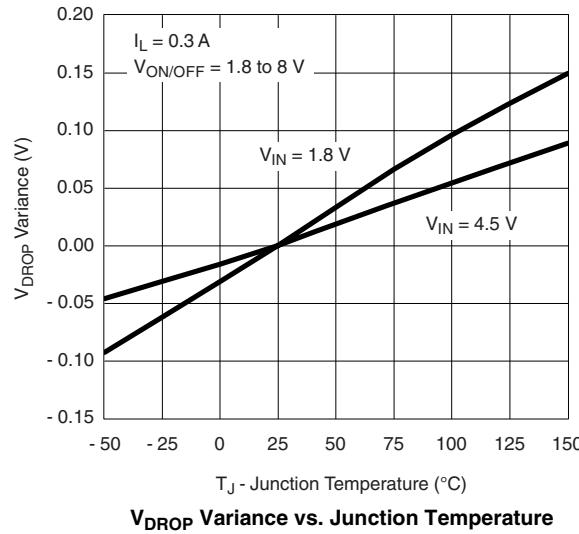
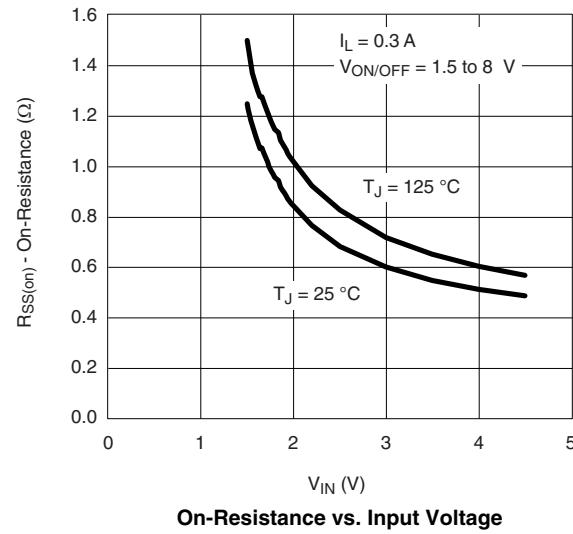
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Reverse Leakage Current	I_{FL}	$V_{IN} = 8\text{ V}$, $V_{ON/OFF} = 0\text{ V}$			1	μA
Diode Forward Voltage	V_{SD}	$I_S = - 0.15\text{ A}$		0.85	1.2	V
ON Characteristics						
Input Voltage Range	V_{IN}		1.8		8	V
On-Resistance (P-Channel) at 1 A	$R_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}$, $V_{IN} = 4.5\text{ V}$, $I_D = 0.43\text{ A}$		0.500	0.625	Ω
		$V_{ON/OFF} = 1.5\text{ V}$, $V_{IN} = 2.5\text{ V}$, $I_D = 0.36\text{ A}$		0.710	0.890	
		$V_{ON/OFF} = 1.5\text{ V}$, $V_{IN} = 1.8\text{ V}$, $I_D = 0.3\text{ A}$		1.0	1.25	
On-State (P-Channel) Drain Current	$I_{D(on)}$	$V_{IN-OUT} \leq 0.2\text{ V}$, $V_{IN} = 5\text{ V}$, $V_{ON/OFF} = 1.5\text{ V}$	1			A
		$V_{IN-OUT} \leq 0.3\text{ V}$, $V_{IN} = 3\text{ V}$, $V_{ON/OFF} = 1.5\text{ V}$	0.8			

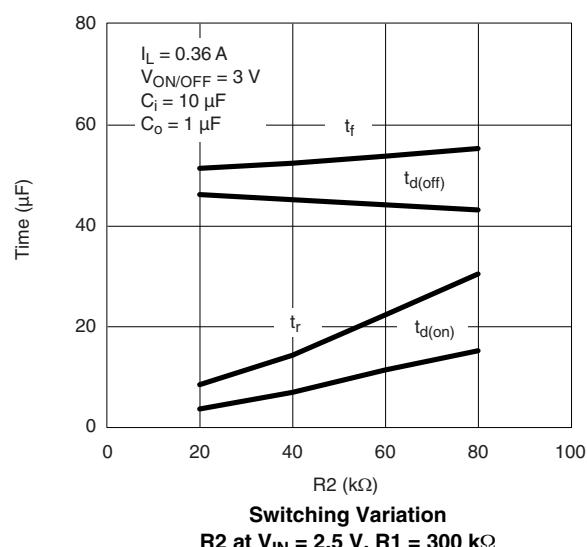
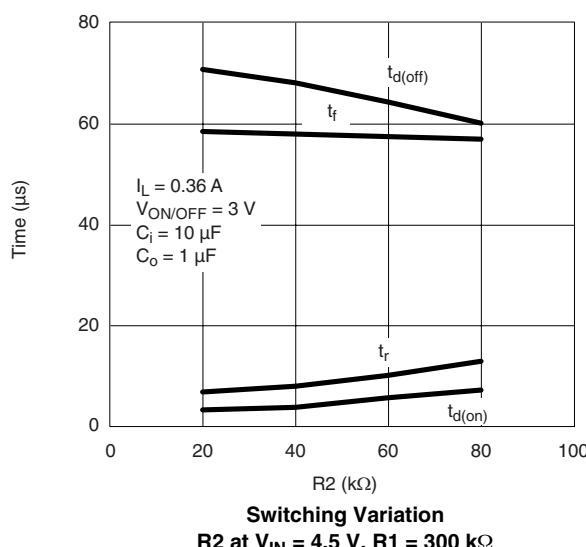
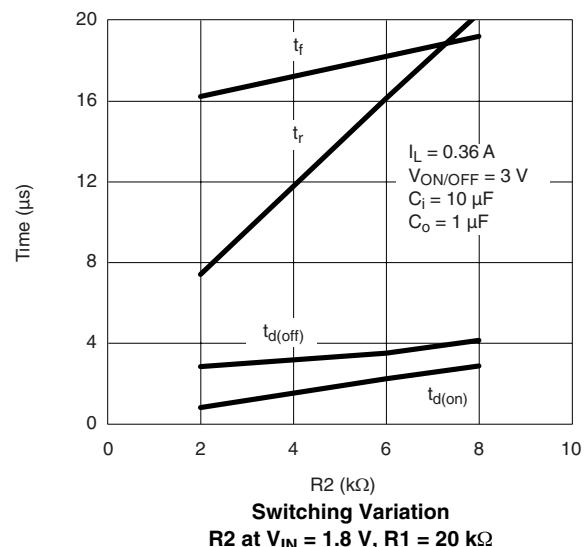
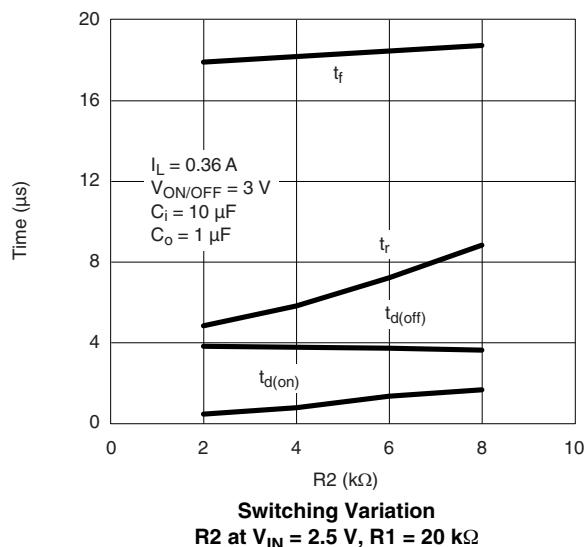
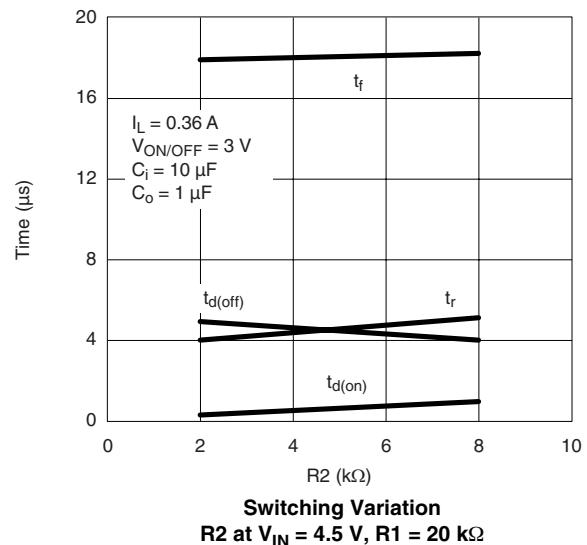
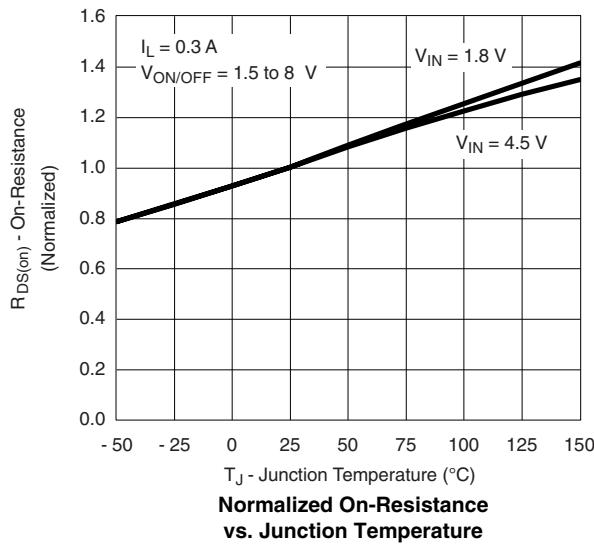
Notes:

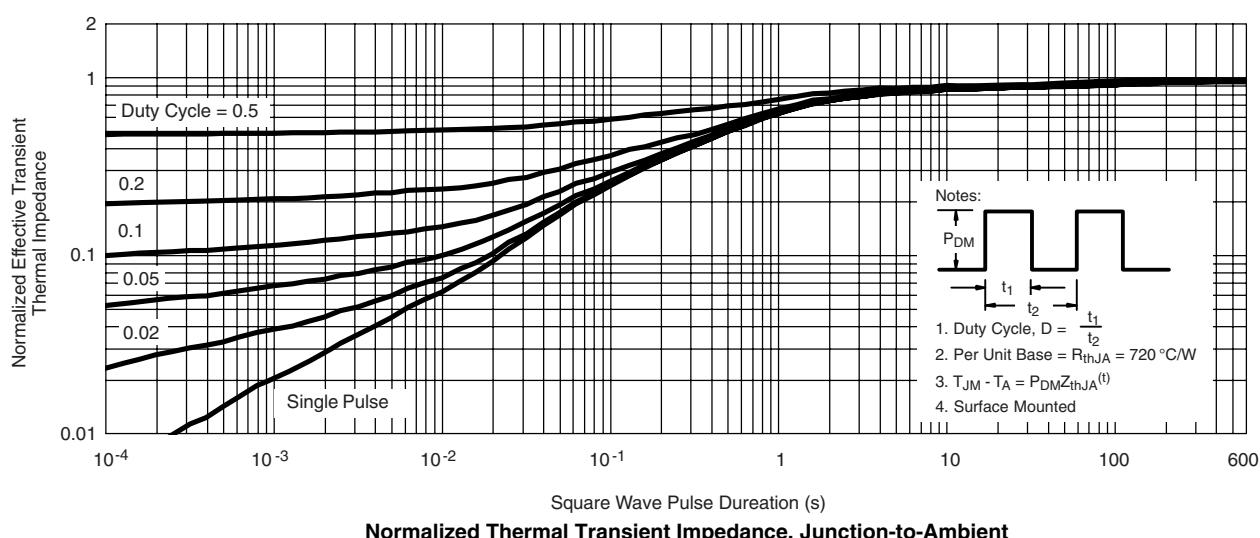
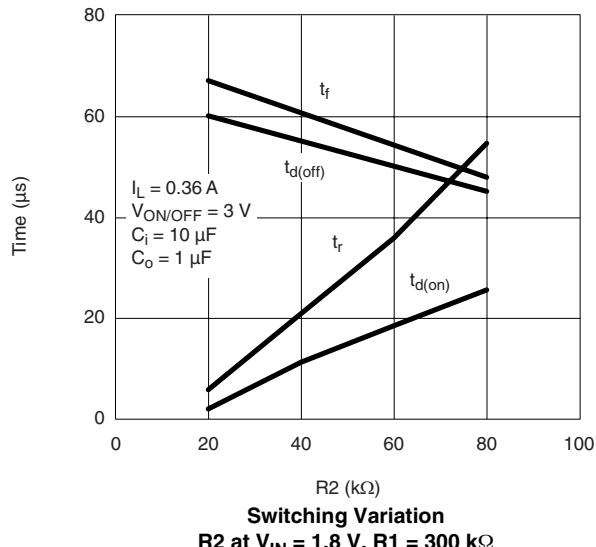
a. Surface Mounted on FR4 board.
b. $V_{IN} = 8\text{ V}$, $V_{ON/OFF} = 8\text{ V}$, $T_A = 25^\circ\text{C}$.
c. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 V_{DROP} vs. I_L at $V_{IN} = 4.5$ V

 V_{DROP} vs. I_L at $V_{IN} = 2.5$ V

 V_{DROP} vs. I_L at $V_{IN} = 1.8$ V

 V_{DROP} vs. I_L at $V_{IN} = 0.5$ V

 V_{DROP} Variance vs. Junction Temperature

On-Resistance vs. Input Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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